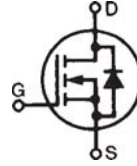
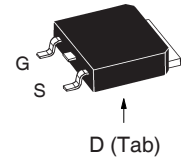
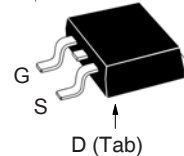
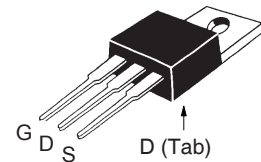


**Depletion Mode  
MOSFET**
**IXTY1R6N50D2  
IXTA1R6N50D2  
IXTP1R6N50D2**
 $V_{DSX} = 500V$   
 $I_{D(on)} \geq 1.6A$   
 $R_{DS(on)} \leq 2.3\Omega$ 
**N-Channel**


Symbol	Test Conditions	Maximum Ratings	
$V_{DSX}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{GSX}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$P_D$	$T_C = 25^\circ\text{C}$	100	W
$T_J$		- 55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		- 55 ... +150	$^\circ\text{C}$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ\text{C}$
$M_d$	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
<b>Weight</b>	TO-252	0.35	g
	TO-263	2.50	g
	TO-220	3.00	g

**TO-252 (IXTY)**

**TO-263 AA (IXTA)**

**TO-220AB (IXTP)**


G = Gate      D = Drain  
S = Source    Tab = Drain

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSX}$	$V_{GS} = -5V, I_D = 250\mu\text{A}$	500		V
$V_{GS(off)}$	$V_{DS} = 25V, I_D = 100\mu\text{A}$	- 2.0		V
$I_{GSX}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$ nA
$I_{DSX(off)}$	$V_{DS} = V_{DSX}, V_{GS} = -5V$ $T_J = 125^\circ\text{C}$			2 $\mu\text{A}$ 25 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 0V, I_D = 0.8A$ , Note 1			2.3 $\Omega$
$I_{D(on)}$	$V_{GS} = 0V, V_{DS} = 25V$ , Note 1	1.6		A

**Features**

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 30\text{V}$ , $I_D = 0.8\text{A}$ , Note 1	1.00	1.75	S
$C_{iss}$	$V_{GS} = -10\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		645	pF
$C_{oss}$			65	pF
$C_{rss}$			16.5	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = \pm 5\text{V}$ , $V_{DS} = 250\text{V}$ , $I_D = 0.8\text{A}$ $R_G = 5\Omega$ (External)		25	ns
$t_r$			70	ns
$t_{d(off)}$			35	ns
$t_f$			41	ns
$Q_{g(on)}$	$V_{GS} = 5\text{V}$ , $V_{DS} = 250\text{V}$ , $I_D = 0.8\text{A}$		23.7	nC
$Q_{gs}$			2.2	nC
$Q_{gd}$			13.8	nC
$R_{thJC}$	TO-220		0.50	1.25 $^\circ\text{C/W}$ $^\circ\text{C/W}$
$R_{thCS}$				

### Safe-Operating-Area Specification

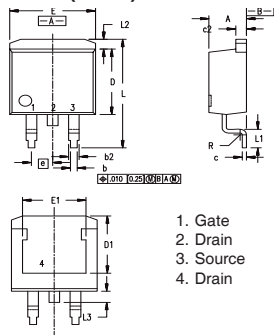
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 400\text{V}$ , $I_D = 0.15\text{A}$ , $T_C = 75^\circ\text{C}$ , $T_p = 5\text{s}$	60		W

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{SD}$	$I_F = 1.6\text{A}$ , $V_{GS} = -10\text{V}$ , Note 1		0.8	1.3 V
$t_{rr}$	$I_F = 1.6\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ , $V_{GS} = -10\text{V}$		400	ns
$I_{RM}$			9.16	A
$Q_{RM}$			1.83	$\mu\text{C}$

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### TO-263 (IXTA) Outline



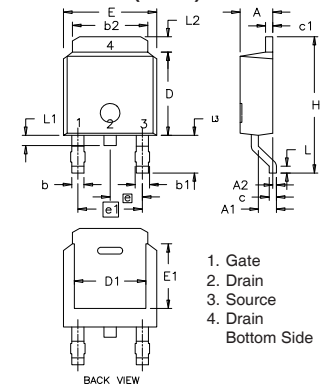
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070

1. Gate
2. Drain
3. Source
4. Drain

### PRELIMINARY TECHNICAL INFORMATION

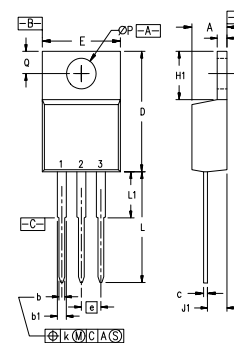
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

### TO-252 AA (IXTY) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28	BSC	0.090	BSC
e1	4.57	BSC	0.180	BSC
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

### TO-220 (IXTP) Outline



- Pins: 1 - Gate  
3 - Source  
2 - Drain  
4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100	BSC	2.54	BSC
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

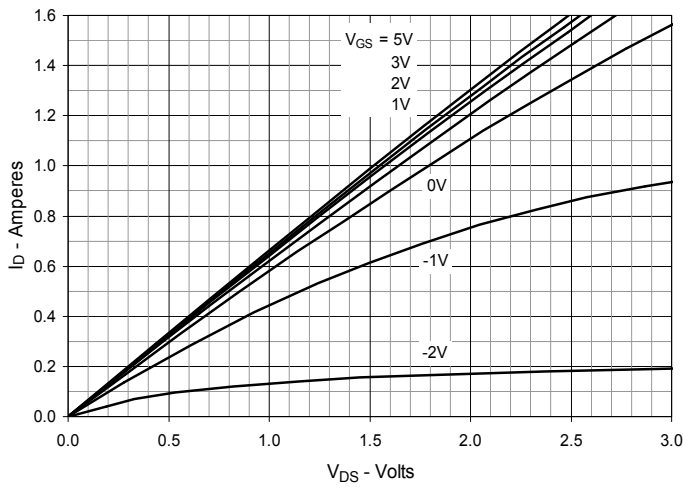


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

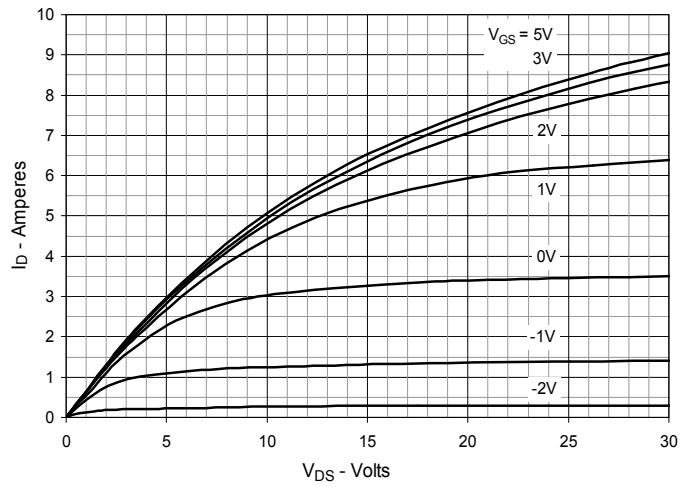


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

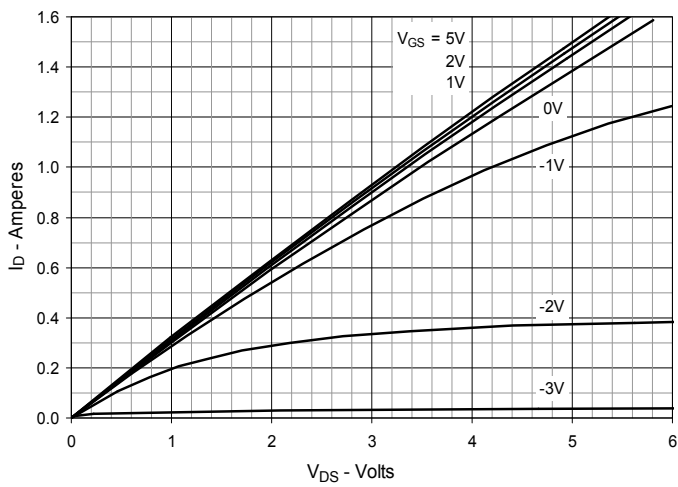


Fig. 4. Drain Current @  $T_J = 25^\circ\text{C}$

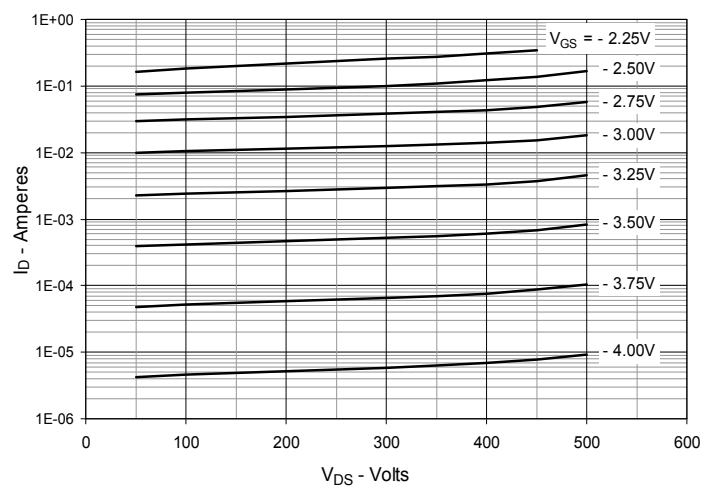


Fig. 5. Drain Current @  $T_J = 100^\circ\text{C}$

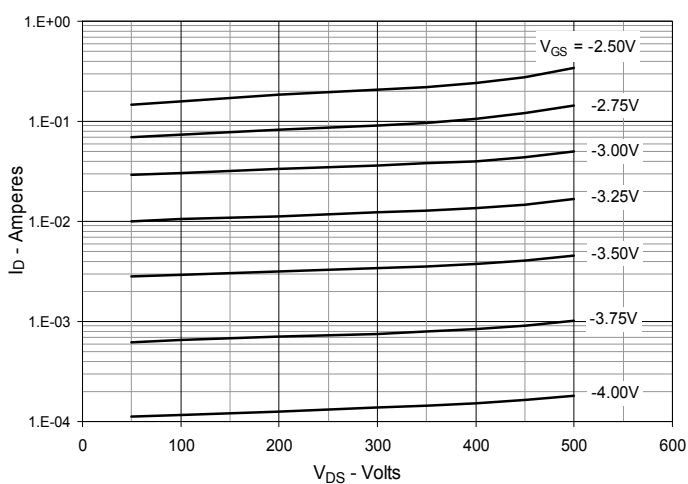


Fig. 6. Dynamic Resistance vs. Gate Voltage

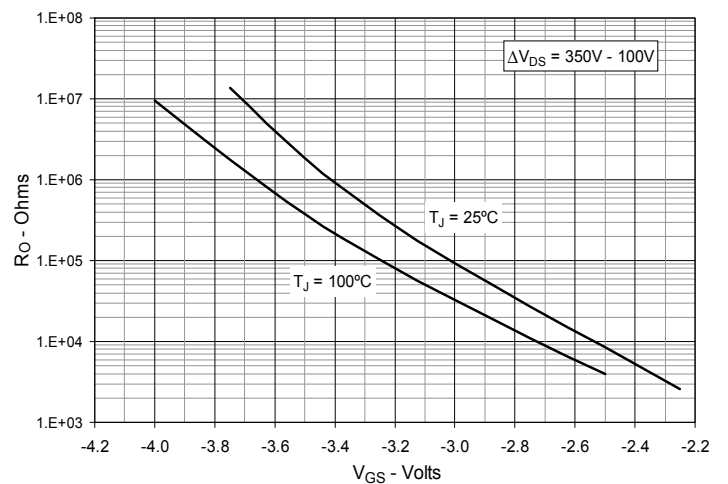


Fig. 7. Normalized  $R_{DS(on)}$  vs. Junction Temperature

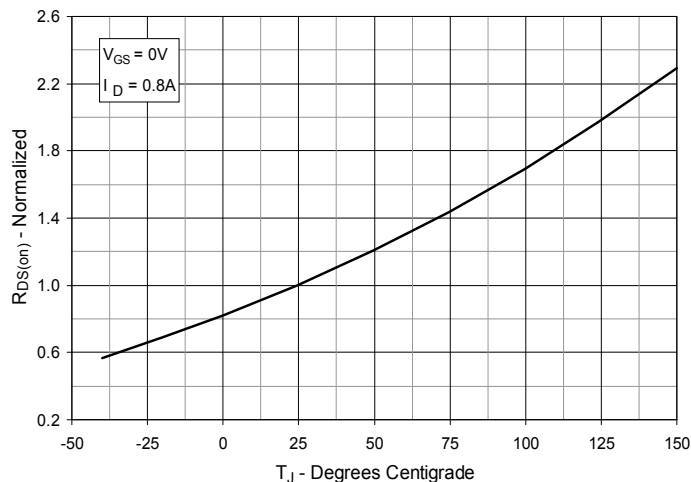


Fig. 8.  $R_{DS(on)}$  Normalized to  $I_D = 0.8A$  Value vs. Drain Current

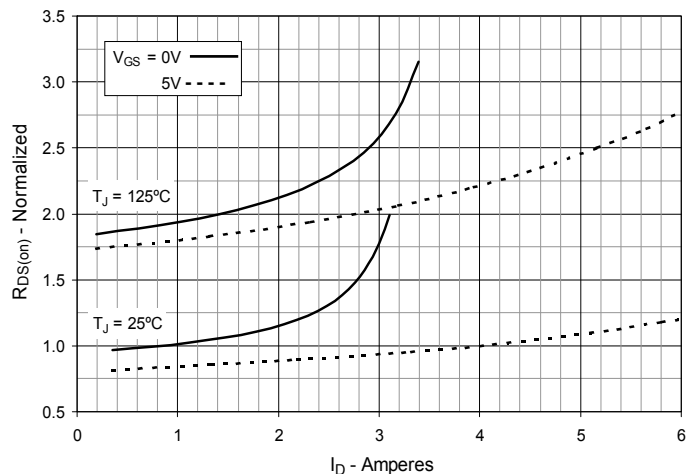


Fig. 9. Input Admittance

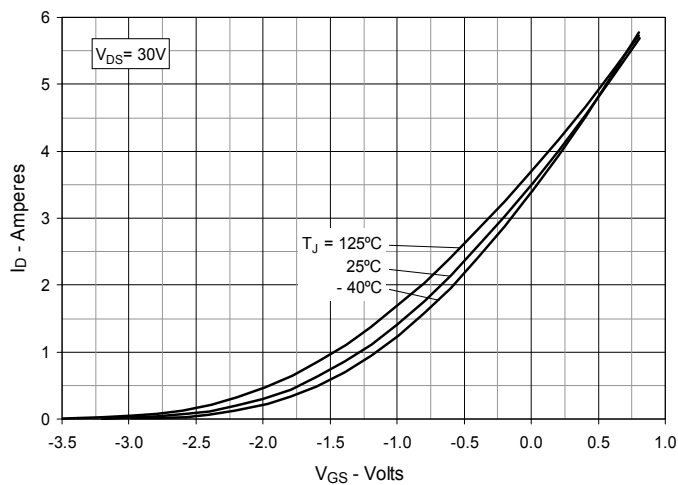


Fig. 10. Transconductance

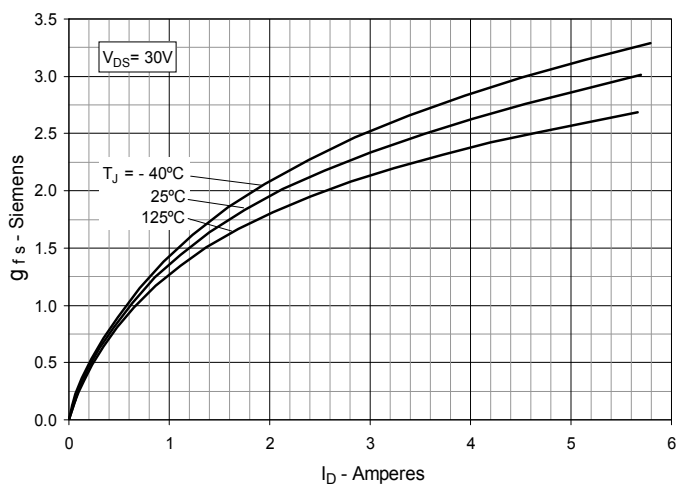


Fig. 11. Breakdown and Threshold Voltages vs. Junction Temperature

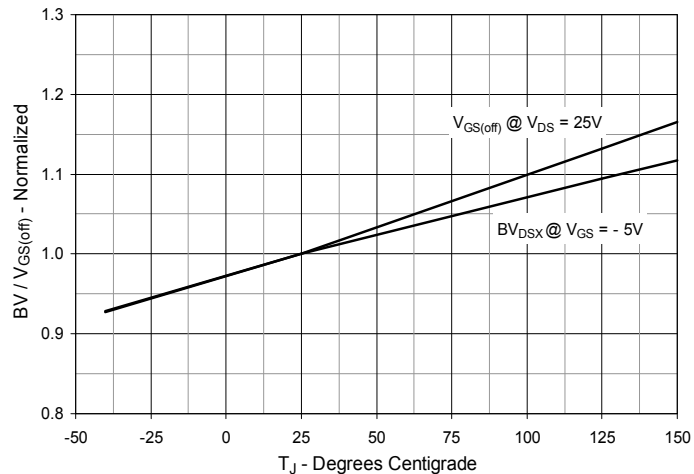


Fig. 12. Forward Voltage Drop of Intrinsic Diode

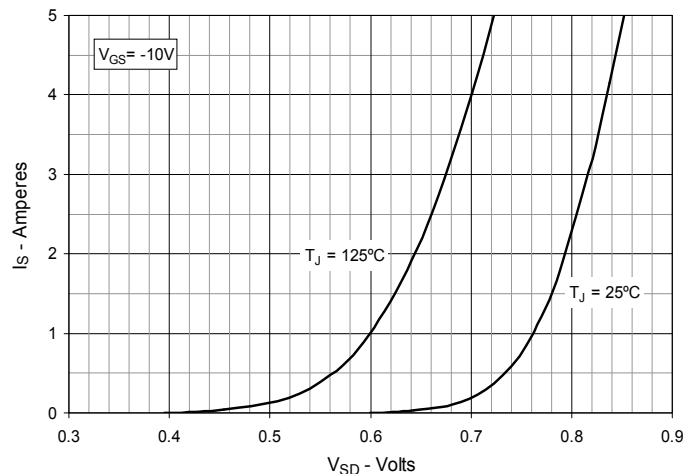


Fig. 13. Capacitance

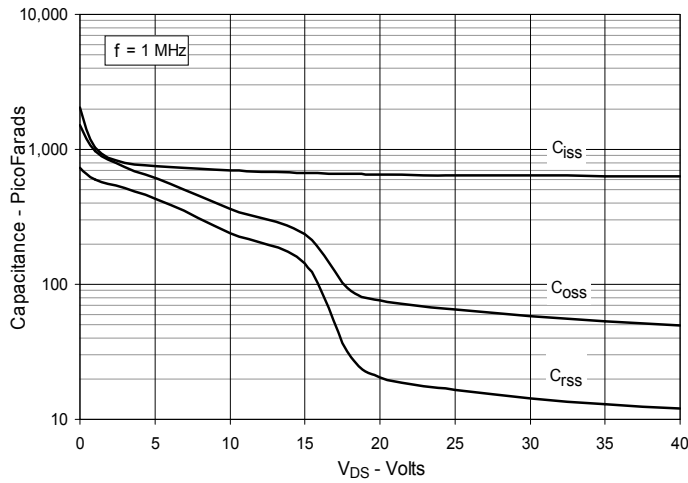


Fig. 14. Gate Charge

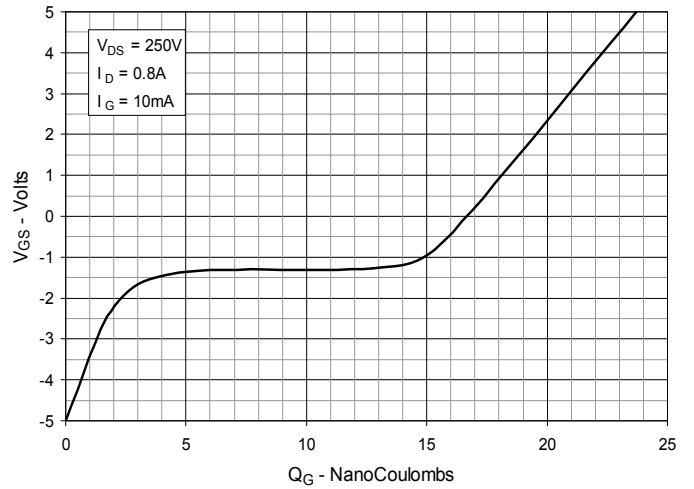


Fig. 15. Forward-Bias Safe Operating Area  
@  $T_C = 25^\circ\text{C}$

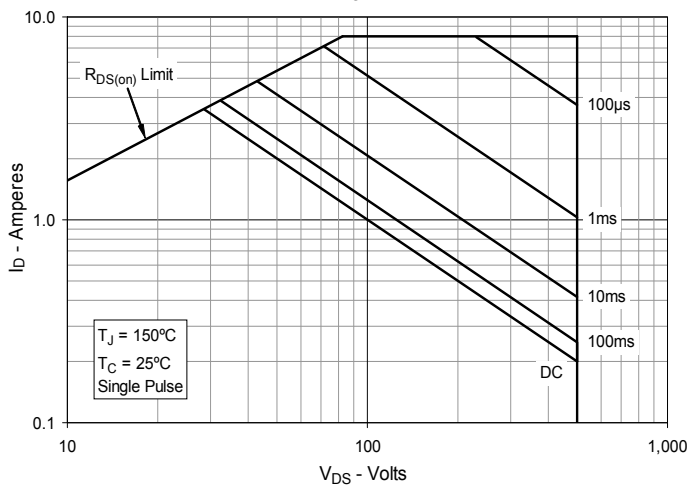


Fig. 16. Forward-Bias Safe Operating Area  
@  $T_C = 75^\circ\text{C}$

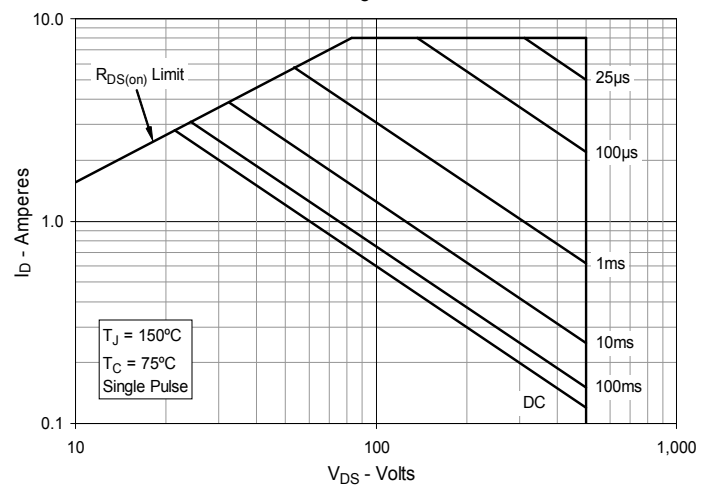


Fig. 17. Maximum Transient Thermal Resistance

